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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Appellant:

Confirmation No.: 9152

Kazunari HONMA et al.

Group Art Unit: 2814

Application No.: 10/631,858

Examiner: Howard WEISS

Filed: August 1, 2003

Attorney Dkt. No.: 024808-00014

For: DIELECTRIC DEVICE HAVING DIELECTRIC FILM TERMINATED  
BY HALOGEN ATOMS

**REQUEST FOR ACKNOWLEDGEMENT OF  
CONSIDERATION OF DISCLOSED INFORMATION**

Mail Stop: Issue Fee  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Date: March 22, 2007

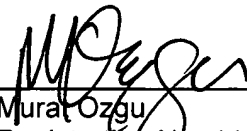
Sir:

An Information Disclosure Statement with Form PTO/1449 was filed in the above-captioned patent application on August 1, 2003. Applicants have not yet received a copy of the Form PTO/1449 initialed by the Examiner to acknowledge all the cited disclosed information was considered by the Examiner.

The Examiner is requested to initial and return to the undersigned a copy of the subject Form PTO/1449 indicating the cited reference "Item I "Low Temperature Deposition Material", Section 4 "New Deposition Material", Ferroelectric Memory Advanced Process, September 13, 1999" has been considered. A concise explanation of the reference, as requested by the Examiner in the June 13, 2005 Office Action, was included with the Response filed September 13, 2005. For the convenience of the Examiner, a copy of the PTO/1449 is attached.

Should there be any questions concerning this communication, please telephone the undersigned attorney at the telephone number set forth below. Please charge any fee deficiency or credit any overpayment to Deposit Account No. 01-2300, referencing docket No. 024808-00014.

Respectfully submitted,

  
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Murat Ozgu  
Registration No. 44,275

Customer Number: 004372  
ARENT FOX LLP  
1050 Connecticut Avenue, N.W., Suite 400  
Washington, D.C. 20036-5339  
Tel: (202) 857-6000; Fax: (202) 638-4810  
MO:elp  
Enclosure: PTO 1449



FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

ATTORNEY DOCKET NUMBER

024808-00014

NEW PATENT  
APPLICATION

## LIST OF REFERENCES CITED BY APPLICANT

(Use several sheets if necessary)

APPLICANT

Kazunari HONMA, et al.

FILING DATE

August 1, 2003

GROUP

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION		
							YES	NO	PART.
	AG	11-068057	March 9, 1999	Japan					X
	AH	2001-072416	March 21, 2001	Japan					X
	AI	11-080181	March 26, 1999	Japan					X
	AJ								
	AK								
	AL								

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

	AM	Item I "Low Temperature Deposition Material" Section 4 "New Deposition Material" Ferroelectric Memory Advanced Process September 13, 1999
	AN	
	AO	

EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.